



# SILICON SWITCHING DIODES

Screening in reference to MIL-PRF-19500 available

### **DESCRIPTION**

This 1N643, 1N662 and 1N663 series of JEDEC registered switching/signal diodes are metallurgically bonded and hermetically sealed. These low capacitance diodes feature double-plug construction in a DO-35 package. They are particularly suited to applications where medium speed switching is required. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website http://www.microsemi.com.

### **FEATURES**

- JEDEC registered 1N643, 1N662 and 1N663.
- Metallurgically bonded.
- Hermetically sealed.
- Double-plug construction.
- Up-screening available in reference to MIL-PRF-19500. (See part nomenclature for all available options.)
- RoHS compliant versions available.

### **APPLICATIONS / BENEFITS**

- Flexible axial-lead mounting terminals.
- High frequency data lines:
  - RS-232 & RS-422 interface networks
  - Ethernet 10 Base T links
  - Switching core drivers
  - Local area networks
  - Computers

# **MAXIMUM RATINGS**

Parameters/Test Conditions		Symbol	Value	Unit
Junction Temperature		TJ	-65 to +150	°C
Storage Temperature		$T_{STG}$	-65 to +175	°C
Thermal Impedance		$Z_{\Theta JX}$	70	°C/W
Reverse Voltage, RMS Value	1N643	$V_r$	200	V(pk)
	1N662 & 1N663		100	
Reverse Voltage, Working Peak	1N643	$V_{RWM}$	175	V(pk)
			80	
Forward Current, Surge Peak	1N662 & 1N663	I <sub>FSM</sub>	500	mA
@ 8.3 ms				
Average Forward Current	1N643 & 1N662 (1)	Io	40	mA
	1N663 <sup>(2)</sup>		100	
Solder Pad Temperature @ 10 s m	$T_SP$	260	°C	

Notes: 1. Derate 1N643 and 1N662 at 0.32 mA/ $^{\circ}$ C above T<sub>A</sub> = 25  $^{\circ}$ C.

2. Derate 1N663 at 0.48 mA/ $^{\circ}$ C above T<sub>A</sub> = 25  $^{\circ}$ C.



**DO-35 Package** 

MSC - Lawrence

6 Lake Street. Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

#### MSC - Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

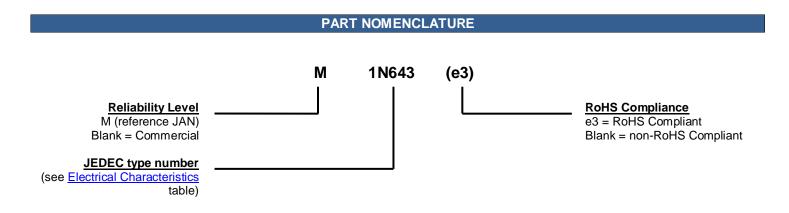
#### Website:

www.microsemi.com



# **MECHANICAL and PACKAGING**

- · CASE: Hermetically sealed glass case.
- TERMINALS: Tin/lead finished copper clad steel or RoHS compliant matte-tin finish available.
- MARKING: Alphanumeric.
- POLARITY: Cathode end is banded.
- TAPE & REEL option: Standard per EIA-296 (add "TR" suffix to part number). Consult factory for quantities.
- WEIGHT: 0.2 grams.
- See <u>Package Dimensions</u> on last page.



SYMBOLS & DEFINITIONS			
Symbol	Definition		
I <sub>F</sub>	Forward Current.		
Io	Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.		
I <sub>R</sub>	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.		
$T_{SP}$	Temperature Solder Pad: The maximum solder temperature that can be safely applied to the terminal.		
V <sub>F</sub>	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.		
$V_{RWM}$	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range excluding all transient voltages (ref JESD282-B). Also sometimes known as PIV.		
$V_{WM}$	Working Peak Voltage: The maximum peak voltage that can be applied over the operating temperature range. This is also referred to as Standoff Voltage.		
$Z_{\Theta JX}$	Thermal Impedance: The thermal impedance junction to reference point.		



# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise specified)

TYPE NUMBER	Forward Voltage V <sub>F</sub> (See Note 1)	Reverse Current I <sub>R</sub> @ V <sub>R</sub> = 10 V		Capacitance C	Reverse Recovery Time T <sub>rr</sub>
		T <sub>A</sub> @ 25 ℃	T <sub>A</sub> @ 100 °C		(See Note 2)
		(I <sub>R</sub> @ 25 ℃)			
	V (max)	nA (max)	μΑ (max)	pF (max)	ns (max)
1N643	1.0	25 (100 μA @ 200 V)	15 @ 100 V	3 @ 175 V	300
1N662	1.0	25 (100 μA @ 100 V)	100 @ 50 V	3 @ 80 V	500
1N663	1.0	25 (100 μA @ 100 V)	50 @ 75 V	3 @ 80 V	500

**NOTES:** 1.  $I_F$  = 10 mA for 1N643 and 1N662;  $I_F$  = 100 mA for 1N663.

<sup>2.</sup> Test condition B:  $I_F$  = 5 mA;  $I_R$  = 17.5 mA;  $R_L$  = 2300 ohms +/- 10 %; C = 40 pF, max.



# **GRAPHS**

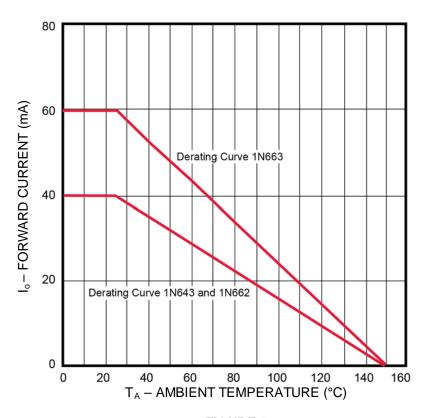
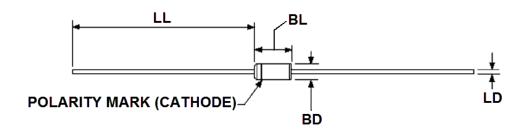


FIGURE 1
Average Rectified Current vs Ambient Temperature



# **PACKAGE DIMENSIONS**



	Dimensions				
Symbol	Inch		Millimeters		
	Min	Max	Min	Max	
BD	.056	075	1.42	1.90	
BL	.140	.180	3.56	4.57	
LD	.018	.022	.046	.056	
LL	1.000	1.500	25.40	38.10	

### NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. The minimum body diameter shall be maintained over .15 inch (3.81 mm) inch of body length.
- 4. The specified lead diameter applies in the zone between .050 inch (1.27 mm) and the end of the lead. Outside of this zone the lead diameter shall not exceed LD.
- 5. Both leads shall be within the specified dimension.
- 6. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microsemi: